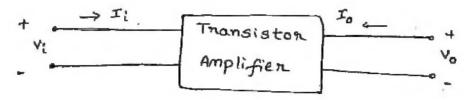
BJT AMPLIFIERS

H-Panameter Representation of a Transiston

A transistor can be treated as a two-part Network



Hene Ii = Input connent to the Amplifien

Vi = Input voitage to the Amplifier

To = output connent of the Amplifien

Vo = output . voitage of the Amplifien

Transistor is a current operated device.

Here input voltage Vi and output corrent to are the dependent variables.

Input current Ii and output voitage vo are Independent Variables.

$$V_i = f_i \left(I_i, V_o \right).$$

$$I_o = f_2 \left(I_i, V_o \right).$$

this can be written in the equation form as follows

the above equation can also be written using alphabetic Notations

$$V_i = hi I_i + h_0 V_0$$

$$I_0 = h_f I_i + h_0 V_0$$

Definitions of h- parameter:

The parameters in the above equation are defined as follows

$$h_{ii} = h_i = \frac{V_i}{T_i} \bigg|_{V_0 = 0} = Input Mesistance with output$$

$$h_{12} = h_n = \frac{V_i}{I_0}$$

Revense voitage transfer ratio

with input open cincuited.

 $h_{12} = h_0 = \frac{V_i}{I_0}$

Short cincuited.

$$h_{22} = h_0 = \frac{T_0}{V_0} \Big|_{T_1 = 0} = \begin{array}{c} \text{output Admittance with input} \\ \text{open cincuited.} \end{array}$$

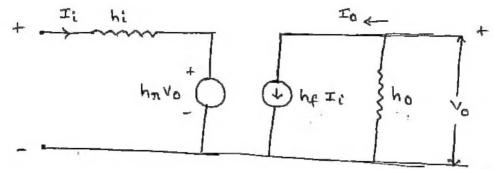
BJT H-panameter model:

Based on the definition of hybrid parameters the mathematical model for two port networks known as h-parameter model (Hybrid Parameter model) can be developed.

The two equations of a transiston is given by
$$V_i = h_i \, T_i \, + \, h_n \, V_0$$

$$T_0 = h_f \, T_i \, + \, h_0 \, V_0$$

Based on above two equations the equivalent circuit on Hybrid Model for transistor can be drawn.

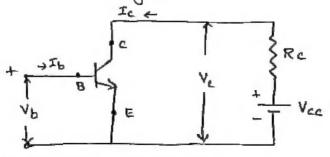


Advantages (on) Benifits of h- panameters

- 1) Real humbers at audio frequencies
- 2) Easy to measure
- 3) can be obtained from the transistor static characteristic curves.
- 4) convinient to use in circuit analysis and design.
- 5) Easily convertable from one configuration to other
- 6) most of the transistor manufacturers sepecify the h-parameters.

H panameter model for CE configuration

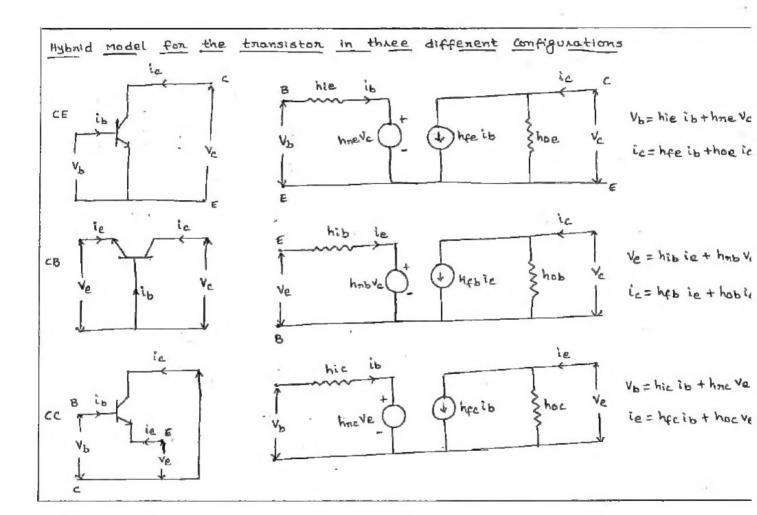
Let us consider the common emitter configuration shown in figure below. The Variables Ib, Ic, Vb and Vc represent total instantaneous connents and Voltages,



Re Fig: simple common emitten

T Vec configuration

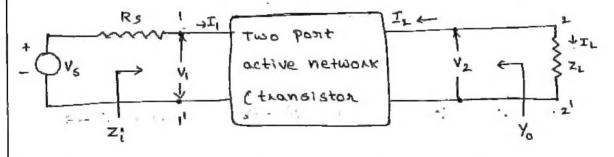
Here Ib - Input corrent Vb - Input voltage Ic - output current Ve - output Voitage h- parameter model for common emitter configuration shown in figure below. Vb = hie Ib + hne Ve Ic = hee Ib + hoe Ve hie = $\frac{\Delta V_B}{\Delta I_B}$ | $V_c = constant$ = $\frac{V_b}{I_b}$ | $V_c = constant$ where hne = $\frac{\Delta V_B}{\Delta V_C}$ = $\frac{V_b}{V_C}$ = $\frac{V_b}{V_c}$ | $I_b = constant$ $hfe = \frac{\Delta Tc}{\Delta TB} \bigg|_{V_c = constant} = \frac{ic}{ib} \bigg|_{V_c = constant}$ $hoe = \frac{\Delta I_c}{\Delta V_c} \Big|_{IB = constant} = \frac{ic}{V_c} \Big|_{Ib = constant}$



Typical h-pariameter values for a transistor				
Panameten 2	CE	cc	cB	
hi	1100 A	11001	22 1	
hn	25x10-4	1	3 x 15 4	
her- 19	50	-51	-0.98	
ho	25 MA/V	25 MA/V	0.49 MA/V	

Analysis of a transistor amplifier circuit using h-parameter model.

by connecting an external load and signal sounce as indicated in figure below and biasing the transistor properly.



The hybrid parameter model for above network is shown in figure below.

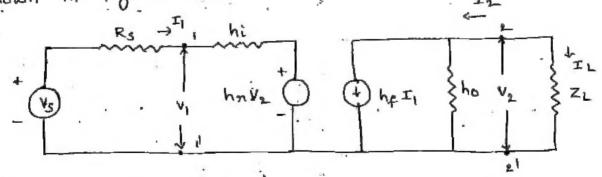


Fig: Transiston hybrid parameter model.

Cunnent Gain (on) Connent Amplification A:

For a transistor amplifier the current gain Az is defined as the natio of output current to input current.

$$A_{I} = \frac{I_{L}}{I_{l}} = -\frac{I_{2}}{I_{l}}$$

From the circuit $I_2 = h_f I_1 + h_0 V_2 \longrightarrow 0$ $V_2 = I_L Z_L = -I_2 Z_L \longrightarrow (2)$

Sub ② in ①

$$I_2(1+Z_Lh_0) = hf I_1 \Rightarrow \frac{I_2}{I_1} = \frac{hf}{1+Z_Lh_0}$$

$$A_{I} = \frac{-I_{2}}{I_{1}} = \frac{-hf}{1 + Z_{L}ho}$$

AI

- hfc

2) Input Impedance zi

In the circuit Rs is the signal source resistance the impedance seen when looking in to the amplifien terminals (1,1) is the amplifier input impedance zi

$$z_i = \frac{v_i}{T_i}$$

From figure V1 = h1 I1 + h 1 V2

So
$$Z_1 = \frac{h_1 T_1 + h_1 N_2}{T_1} = h_1 + h_1 \frac{N_L}{T_1} \rightarrow 0$$
 $V_2 = -T_2 Z_L = A_1 Z_1 Z_L$
 $V_2 = -T_2 Z_L = A_1 Z_1 Z_L$
 $Z_1 = h_1 + h_1 A_1 Z_L$
 $Z_2 = h_2 + h_2 A_1 Z_L$
 $Z_3 = h_3 + h_2 A_1 Z_L$
 $Z_4 = h_1 - h_1 A_1 Z_L$
 $Z_4 = h_2 - h_1 A_2 A_1$
 $Z_4 = h_1 - h_1 A_2 A_2$
 $Z_4 = h_2 - h_1 A_2$
 $Z_4 = h_1 A_1 A_2$
 $Z_4 = h_1 A_1$

CB

CC

$$V_0 = \frac{\Gamma_2}{V_2}$$
 with $V_S = 0$ and $R_L = \infty$

from the circuit
$$I_2 = h_f I_1 + h_0 Y_2$$

Dividing by
$$V_2$$
, $\frac{T_1}{V_2} = h_f \frac{T_1}{V_2} + h_0 \longrightarrow 0$

with Vs = 0, by KVL in input cincuit

Hence
$$\frac{I_1}{V_2} = \frac{h_1}{R_5 + h_1}$$

NOW EQ
$$0 \Rightarrow \frac{T_2}{V_2} = \frac{-h_f h_n}{R_5 + h_i} + h_0$$

$$\Rightarrow y_0 = h_0 - \frac{h_f h_R}{R_S + h_L}$$

CE

CB

CC

$$A_{VS} = \frac{V_2}{V_S} = \frac{V_2}{V_1} \frac{V_1}{V_S} \Rightarrow A_{VS} = A_V \frac{V_1}{V_S}$$

$$V_1 = \frac{V_s z_i}{R_s + z_i} \implies \frac{V_1}{V_s} = \frac{z_i}{R_s + z_i}$$

$$Avs = \frac{A \pm RL}{z_1^2} \times \frac{ZL}{R_5 + ZL} = \frac{A \pm RL}{R_5 + ZL}$$

sf
$$R_s = 0$$
 then $Av_s = \frac{AIRL}{Z_i} = Av$.

6) conent Amplification (AIS)

$$A_{IS} = \frac{-I_2}{I_5} = \frac{-I_2}{I_1} \cdot \frac{I_1}{I_5} = A_I \cdot \frac{I_1}{I_5}$$

The modified input cincuit using Nonton's equivalent cincuit for the sounce for the calculation of AIS

$$\left(z_{L} = R_{L} \right)$$

⇒ In cc configuration Connent gain A= = -Input Impedance zi = hic - hec hac Voitage gain Av = Ax ZL output Admittance Yo = hoc - hec hac Convension formulae for hybrid parameters ~ CC CB $hib = \frac{hie}{1 + hfe}$ hic = hie hnb = hie hoe - hne hac = 1 hfb = -hfe hec = - (1+ hee) hob = hoe hoc = hoe 1) characteristics of common emitter Amplifier) correct gain AI is high for RL < LOKA 2) the voltage gain is high for normal values of Load nesistance R∟ 3) The input nesistance Ri is medium

4) The output resistance Ro is moderately high

Applications of common emitter amplifier:

2)

- 1. of the three configurations ce amplifier alone is capable of providing both voltage gain and current gain.
- 2. The output mesistance Ro and input mesistance Ri are moderately high
- 3. CE amplifien is widely used for Amplification purpose characteristics of common Base Amplifien:
- 1. Connent gain is less than unity and its magnitude decreases with the increase of load nesistance RL
- 2. Voitage gain Av is high for normal values of RL
- 3. The input nesistance Ri is the lowest of all the three configurations.
- 4. The output resistance Ro is the highest of all the three configurations.

Applications of common base Amplifier

The CB Amplifien is not commonly used for Amplification pumpose. It is used for

- 1) Matching a very low impedance source.
- 2) as a non inventing amplifien with voltage gain exceeding unity
- 3) For driving a high impedance load
- 4) As a constant current source.
- 3) characteristics of common collector Amplifier

 1. For low value of RL (<10KL) The current gain Az 1s

 high and almost equal to that of a CE amplifier

- 2. The voltage gain Av is less than unity.
- 3. The input nesistance is the highest of all the three configurations.
- 4 The output nesistance is the lowest of all the three configurations.

Applications of common collector Amplifier:

1. The cc Amplifier is widely used as a buffer stage between a high impedance source and low impedance load. (cc Amplifier is called emitter follower)

companison of Transiston Amplifier Configurations.

the characteristics of three configurations are summarized in table below. Here the quantities AI, AV, Ri, Ro and Ap (Power gain) are calculated for RL = Rs = 3 km

quantity	<b< th=""><th>CC</th><th>ĽE</th></b<>	CC	ĽE
Ax	۵،98	47.5	-46.5
A _v	131	ø·9 8 9	-131
	128,38	46.98	6091.5
Ap Rt ·	22.6 A	144 KA	1065 J
	1.72MA	80.5A	45.5 KM
Ro	1.72MA	80.07	

Simplified CE Hybrid model (02) Approximate CE Hybrid model (Approximate Analysis):

As the h parameters themselves vary widely for the same type of transistor. It is justified to make approximations and simplify the expressions for AI, AV, Ap, Ri and Ro.

The behaviour of the transistor circuit can be obtained by using the simplified hybrid model. The h-parameter equivalent circuit of the transistor in the CE configuration is shown in figure below.

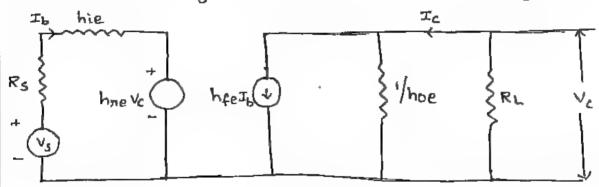


Fig: Exact -CE Hybrid Model.

Hene I is in parallel with RL hoe

The Panallel Combination of two unequal impedances is approximately equal to the lower value le RL. Hence if $\frac{1}{hoe} >> RL$, then the term hoe may be neglected hoe provided that hoe RL << 1

If hoe is omitted, the collector correct Ic is given by $I_C = h_C I_D$.

generated in the emitten cincuit is

hne $|V_C|$ = hne I_C RL = hne hfe I_D RL Since hne hfe \approx 0.01, this voltage may be neglected in companison with the voltage drop across hie. ie hie I_D provided that R_L is not too large. It is the load mesistance R_L is small it is possible to neglect the parameter hne and hoe and the approximate equivalent circuit is obtained as shown in figure below.

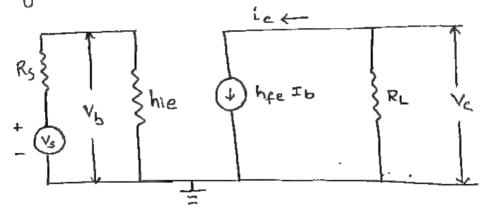


Fig: Approximate CE Hybrid model.

1) CULLENT Gain (AI):

the current gain for CE configuration is

$$A_{I} = \frac{-hfe}{1 + hoe R_{L}}$$
, of hoe $R_{L} < 0.1$

2) Input Impedance (Z1)

By exact analysis
$$Z_i = R_i = \frac{V_i}{I_i}$$

$$V_{1} = hie I_{1} + hne V_{2}$$

$$ZI = \frac{hie I_{1} + hne V_{2}}{I_{1}} = hie + hne \frac{V_{2}}{X_{1}}$$

$$V_{2} = -I_{2}ZL = -X_{2}RL = A_{T}I_{1}RL \qquad \left(\begin{array}{c} \cdot \cdot \cdot A_{T} = \frac{-I_{2}}{X_{1}} \\ \cdot \cdot \cdot \cdot A_{T} = \frac{-I_{2}}{X_{1}} \\ \end{array}\right)$$

$$Z_{1} = hie + hne \frac{A_{T}I_{1}R_{L}}{I_{1}} \qquad \left(\begin{array}{c} \cdot \cdot \cdot \cdot V_{L} = A_{T}I_{1}R_{L} \\ \end{array}\right)$$

$$R_{1} = \left(\begin{array}{c} hie + hne A_{T}R_{L} \\ \end{array}\right)$$

$$R_{1} = hie \left(\begin{array}{c} 1 + \frac{hne A_{T}R_{L}}{hie} \\ \end{array}\right)$$

$$R_{1} = hie \left(\begin{array}{c} 1 + \frac{hne A_{T}R_{L}}{hie} \\ \end{array}\right)$$

$$When A_{2} = -hfe$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 + \frac{o \cdot 5}{h} A_{T}R_{L} hoe \\ \end{array}\right)$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 + \frac{o \cdot 5}{h} A_{T}R_{L} hoe \\ \end{array}\right)$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{o \cdot 5}{h} he R_{L} hoe \\ \end{array}\right)$$

$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{o \cdot 5}{h} he R_{L} hoe \\ \end{array}\right)$$

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$$\Rightarrow R_{1} = hie \left(\begin{array}{c} 1 - \frac{o \cdot 5}{h} he R_{L} hoe \\ \end{array}\right)$$

It is the natio of V_c to I_c with $V_s=0$ and R_c excluded. The simplified cincuit has infinite output impedance because with $V_s=0$ and external voltage sounce applied at output, it is found that $I_b=0$ and hence $I_c=0$

$$R_0 = \frac{V_c}{T_c} = \infty \quad \left(:: T_c = 0 \right)$$

Approximate analysis of CE Amplifier.

connent gain AI = -hee

Input resistance Ri = hie

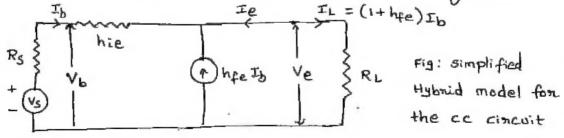
Voltage gain Av = -hee Ri

hie

output resistance Ro = 00

Analysis of cc Amplifier using the approximate Model!

Figure shows the equivalent cincuit of ce Amplifier using the approximate model with the collector grounded, input signal applied between base and ground and load connected between emitter and ground.



$$A_{I} = \frac{I_{L}}{I_{b}} = \frac{(1 + hfe)I_{b}}{I_{b}} = (1 + hfe)$$

$$R_{i} = \frac{V_{b}}{I_{b}} = hie + (1 + hfe) R_{L}$$

3) Voltage gain

$$Av = \frac{Ve}{V_b} = \frac{(1+hfe) I_b R_L}{(hie I_b + (1+hfe) I_b R_L)}$$

$$Av = 1 - \frac{hie}{hie + (1+hfe)R_1}$$

$$Av = 1 - \frac{hie}{Ri}$$
 [" Ri = hie + (1+hfe)RL]

4) output Impedance !-

short circuit corrent =
$$(1+hfe)$$
 Ib = $(1+hfe)$ $\frac{V_s}{R_s+hie}$

open cincuit voltage = Vs

$$\frac{1}{R_s + hie} \Rightarrow R_0 = \frac{hie + R_s}{1 + hfe}$$

output impedance including RL ie Ro = Rol RL

Analysis of CB Amplifier using the approximate model

Figure shows the equivalent cincuit of CB amplifien using the approximate model, with the base grounded, input signal is applied between emitter and base and load connected between collector and base

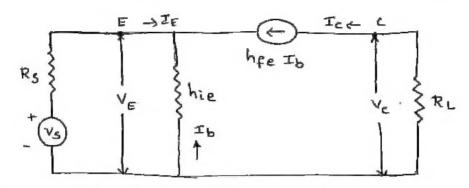


Fig: Simplified Hybrid model for the CB cincuit

1) corrent gain!

From the figure above
$$A_{I} = \frac{-I_{C}}{I_{e}} = \frac{-h_{fe} I_{b}}{I_{e}}$$

$$I_{e} = -(I_{b} + I_{c})$$

$$I_{e} = -(I_{b} + h_{fe} I_{b}) = -(I + h_{fe}) I_{b}$$

$$A_{I} = \frac{-h_{fe} I_{b}}{-(I + h_{fe}) I_{b}} = \frac{h_{fe}}{I + h_{fe}} = -h_{fb}$$

2) Input Resistance:

From figure
$$Ve = -Ibhie$$
, $Ie = -(1+hfe)Ib$

$$R_1 = \frac{hie}{1+hfe} = hib$$

3) voitage gain!

$$A_V = \frac{V_C}{V_C}$$

$$V_c = -I_c R_L = -h_f e I_b R_L$$
 $V_e = -I_b h_i e$

$$A_V = \frac{h_f e R_L}{h_i e}$$

output Impedance

$$R_0 = \frac{V_C}{T_C}$$
 with $V_S = 0$, $R_L = \infty$

with Vs=0, Ie=0 and Ib=0 hence Ic=0

$$\therefore R_0 = \frac{V_C}{o} = \infty$$

Approximate Analysis of CB Amplifier

- 1) coment gain AI = hee = -heb
- 2) Input Resistance Ri = hie = hib
- 3) voltage gain Av = hee RL
- 4) output resistance Ro = 00

Approximate Analysis of CC Amplifier

- i) corrent gain AI = (1+ hfe)
- 2) Input nesistance Ri = hie + (1+hfe) RL
- 3) voltage gain $Av = 1 \frac{hie}{Ri}$
- 4) output Resistance Ro = hie + Rs

 1+ hee